Johji Nishio

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

65	1,120	14	31
papers	citations	h-index	g-index
68	**1,234**	**1.4**	**3.62**
ext. papers	ext. citations	avg, IF	L-index

#	Paper	IF	Citations
65	Single Shockley stacking fault expansion from immobile basal plane dislocations in 4H-SiC. *Japanese Journal of Applied Physics*, **2021**, 60, SBBD01	1.4	3
64	Phase field model of single Shockley stacking fault expansion in 4H-SiC PiN diode. *Japanese Journal of Applied Physics*, **2021**, 60, 024004	1.4	2
63	Conversion of Shockley partial dislocation pairs from unexpandable to expandable combinations after epitaxial growth of 4H-SiC. *Journal of Applied Physics*, **2021**, 130, 075107	2.5	1
62	Origin and Generation Process of a Triangular Single Shockley Stacking Fault Expanding from the Surface Side in 4H-SiC PIN Diodes. *Journal of Electronic Materials*, **2021**, 50, 6504-6511	1.9	1
61	Direct confirmation of structural differences in single Shockley stacking faults expanding from different origins in 4H-SiC PiN diodes. *Journal of Applied Physics*, **2020**, 128, 085705	2.5	6
60	Informative Aspects of Molten KOH Etch Pits Formed at Basal Plane Dislocations on the Surface of 4H-SiC. *Physica Status Solidi (A) Applications and Materials Science*, **2020**, 217, 2000332	1.6	4
59	Photoluminescence Analysis of Individual Partial Dislocations in 4H-SiC Epilayers. *Materials Science Forum*, **2020**, 1004, 376-386	0.4	4
58	Triangular Single Shockley Stacking Fault Analyses on 4H-SiC PiN Diode with Forward Voltage Degradation. *Journal of Electronic Materials*, **2020**, 49, 5232-5239	1.9	5
57	Evaluation of Effect of Mechanical Stress on Stacking Fault Expansion in 4H-SiC P-i-N Diode. *Materials Science Forum*, **2019**, 963, 288-293	0.4	4
56	Dynamics Analysis of Single Shockley Stacking Fault Expansion in 4H-SiC P-i-N Diode Based on Free Energy. *Materials Science Forum*, **2019**, 963, 263-267	0.4	1
55	Initiation of Shockley Stacking Fault Expansion in 4H-SiC P-i-N Diodes. *Materials Science Forum*, **2019**, 963, 280-283	0.4	5
54	Carrier Lifetimes in 4H-SiC Epitaxial Layers on the C-Face Enhanced by Carbon Implantation. *Materials Science Forum*, **2018**, 924, 432-435	0.4	5
53	Dependences of contraction/expansion of stacking faults on temperature and current density in 4H-SiC p[illegible] diodes. *Japanese Journal of Applied Physics*, **2018**, 57, 061301	1.4	20
52	Reduction of background carrier concentration and lifetime improvement for 4H-SiC C-face epitaxial growth. *Japanese Journal of Applied Physics*, **2017**, 56, 081302	1.4	3
51	Reduction in Background Carrier Concentration for 4H-SiC C-face Epitaxial Growth. *MRS Advances*, **2016**, 1, 3631-3636	0.7	2
50	Improvement of 4H-SiC Epitaxial Layers Grown on 2o Offcut Si-Face Substrates. *Materials Science Forum*, **2016**, 858, 133-136	0.4	2
49	Uniformity Improvement in Carrier Concentration on 150 mm Diameter C-Face Epitaxial Growth of 4H-SiC. *Materials Science Forum*, **2015**, 821-823, 169-172	0.4	4

48	Influence of Epi-Layer Growth Pits on SiC Device Characteristics. *Materials Science Forum*, **2015**, 821-823, 177-180	0.4	7
47	Homoepitaxial growth and investigation of stacking faults of 4H-SiC C-face epitaxial layers with a 1° off-angle. *Japanese Journal of Applied Physics*, **2015**, 54, 04DP04	1.4	6
46	Suppression of short step bunching generated on 4H-SiC Si-face substrates with vicinal off-angle. *Journal of Crystal Growth*, **2014**, 401, 673-676	1.6	7
45	Suppression of 3-Inclusion Formation during Growth of 4-SiC Si-Face Homoepitaxial Layers with a 1° Off-Angle. *Materials*, **2014**, 7, 7010-7021	3.5	6
44	Homo-Epitaxial Growth on 2° Off-Cut 4H-SiC(0001) Si-Face Substrates Using H2-SiH4-C3H8 CVD System. *Materials Science Forum*, **2014**, 778-780, 214-217	0.4	5
43	Conversion of Basal Plane Dislocations to Threading Edge Dislocations in Growth of Epitaxial Layers on 4H-SiC Substrates with a Vicinal Off-Angle. *Materials Science Forum*, **2014**, 778-780, 99-102	0.4	4
42	VF Degradation of 4H-SiC PiN Diodes Using Low-BPD Wafers. *Materials Science Forum*, **2014**, 778-780, 851-854	0.4	8
41	C-Face Epitaxial Growth of 4H-SiC on Quasi-150-mm Diameter Wafers with High Throughput. *Materials Science Forum*, **2014**, 778-780, 109-112	0.4	4
40	Growth of silicon carbide epitaxial layers on 150-mm-diameter wafers using a horizontal hot-wall chemical vapor deposition. *Journal of Crystal Growth*, **2013**, 381, 139-143	1.6	10
39	Dependence of 4H-SiC Epitaxial Layer Quality on Growth Conditions with Wafer Size Corresponding to 150 mm. *Materials Research Society Symposia Proceedings*, **2012**, 1433, 59		7
38	Doping Concentration Optimization for Ultra-Low-Loss 4H-SiC Floating Junction Schottky Barrier Diode (Super-SBD). *Materials Science Forum*, **2009**, 615-617, 655-658	0.4	6
37	Design Consideration of High Power Density Inverter with Low-on-voltage SiC-JBS and High-speed Gate Driving of Si-IGBT **2009**,		5
36	Ultralow-Loss SiC Floating Junction Schottky Barrier Diodes (Super-SBDs). *IEEE Transactions on Electron Devices*, **2008**, 55, 1954-1960	2.9	23
35	Simulation, Fabrication and Characterization of 4H-SiC Floating Junction Schottky Barrier Diodes (Super-SBDs). *Materials Science Forum*, **2007**, 556-557, 881-884	0.4	7
34	Optimization of a SiC Super-SBD Based on Scaling Properties of Power Devices. *Materials Science Forum*, **2006**, 527-529, 1179-1182	0.4	4
33	Fabrication of 4H-SiC Floating Junction Schottky Barrier Diodes (Super-SBDs) and their Electrical Properties. *Materials Science Forum*, **2006**, 527-529, 1175-1178	0.4	10
32	Process and Device Simulation of a SiC Floating Junction Schottky Barrier Diode (Super-SBD). *Materials Science Forum*, **2005**, 483-485, 921-924	0.4	9
31	Epitaxial Overgrowth of 4H-SiC for Devices with p-Buried Floating Junction Structure. *Materials Science Forum*, **2005**, 483-485, 147-150	0.4	3

30	Uniformity of 4H-SiC epitaxial layers grown on 3-in diameter substrates. *Journal of Crystal Growth*, **2003**, 258, 113-122	1.6	6
29	SiC Device Limitation Breakthrough with Novel Floating Junction Structure on 4H-SiC. *Materials Science Forum*, **2003**, 433-436, 887-890	0.4	5
28	Epitaxial Growth of High-Quality 4H-SiC Carbon-Face by Low-Pressure Hot-Wall Chemical Vapor Deposition. *Japanese Journal of Applied Physics*, **2003**, 42, L637-L639	1.4	56
27	Epitaxial Growth of (11-20) 4H-SiC Using Substrate Grown in the [11-20] Direction. *Materials Science Forum*, **2002**, 389-393, 195-198	0.4	5
26	Investigation of Residual Impurities in 4H-SiC Epitaxial Layers Grown by Hot-Wall Chemical Vapor Deposition. *Materials Science Forum*, **2002**, 389-393, 215-218	0.4	6
25	Influence of stacking faults on the performance of 4H-SiC Schottky barrier diodes fabricated on (112 0) face. *Applied Physics Letters*, **2002**, 81, 2974-2976	3.4	22
24	Properties of GaN epitaxial layers grown at high growth rates by metalorganic chemical vapor deposition. *Journal of Electronic Materials*, **2001**, 30, 23-26	1.9	5
23	The analysis of contact resistivity between a p-type GaN layer and electrode in InGaN MQW laser diodes. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1999**, 59, 366-369	3.1	2
22	Analysis of transverse modes of nitride-based laser diodes. *IEEE Journal of Selected Topics in Quantum Electronics*, **1999**, 5, 765-770	3.8	10
21	Photoluminescence study of GaN/InGaN multiquantum well structures at room temperature. *Journal of Crystal Growth*, **1998**, 189-190, 128-132	1.6	6
20	Doping characteristics and electrical properties of Mg-doped AlGaN grown by atmospheric-pressure MOCVD. *Journal of Crystal Growth*, **1998**, 189-190, 511-515	1.6	83
19	p-type conduction in as-grown Mg-doped GaN grown by metalorganic chemical vapor deposition. *Applied Physics Letters*, **1998**, 72, 1748-1750	3.4	38
18	Band-gap separation in InGaN epilayers grown by metalorganic chemical vapor deposition. *Journal of Applied Physics*, **1998**, 83, 2860-2862	2.5	14
17	Characterization of InGaN multiquantum well structures for blue semiconductor laser diodes. *Applied Physics Letters*, **1997**, 70, 3431-3433	3.4	30
16	Effects of thermal treatment of low-temperature GaN buffer layers on the quality of subsequent GaN layers. *Journal of Applied Physics*, **1997**, 82, 4877-4882	2.5	78
15	Room Temperature Pulsed Operation of Nitride Based Multi-Quantum-Well Laser Diodes with Cleaved Facets on Conventional C-Face Sapphire Substrates. *Japanese Journal of Applied Physics*, **1996**, 35, L1315-L1317	1.4	202
14	Native point defects in low-temperature-grown GaAs. *Applied Physics Letters*, **1995**, 67, 279-281	3.4	217
13	Theoretical analysis for the segregation in the liquid encapsulated Czochralski system. *Journal of Crystal Growth*, **1994**, 141, 249-255	1.6	3

12	Internal Stress Distribution Estimation in Liquid-Encapsulated Czochralski Grown GaAs Single Crystals Using Measured Temperature on Dummy Crystals. *Japanese Journal of Applied Physics*, **1993**, 32, 716-721	1.4	2
11	Ambient gas constituents and segregation of carbon and boron in LEC GaAs single crystals: the role of water in boric oxide encapsulants. *Journal of Crystal Growth*, **1993**, 134, 97-104	1.6	13
10	Vacuum Bakeout Effect on Ambient Gas in a High Pressure LEC Puller. *Japanese Journal of Applied Physics*, **1992**, 31, 1726-1729	1.4	2
9	Transport restriction effect for gaseous components on the carbon content of LEC GaAs. *Journal of Crystal Growth*, **1991**, 108, 150-156	1.6	4
8	Scatterings of Shallow Threshold Voltage on Si-Implanted WN Self-Alignment Gate GaAs Metal-Semiconductor Field-Effect Transistors on Different Composition 2-Inch Substrates by Growing in Three Kinds of Furnaces. *Japanese Journal of Applied Physics*, **1991**, 30, 2432-2437	1.4	7
7	Gas phase contribution to carbon incorporation and extraction mechanisms for LEC GaAs. *Journal of Crystal Growth*, **1990**, 99, 680-684	1.6	15
6	Influence of melt preparation on residual impurity concentration in semi-insulating LEC GaAs. *Journal of Crystal Growth*, **1989**, 96, 605-608	1.6	18
5	Precise melt composition control for LEC GaAs. *Journal of Crystal Growth*, **1987**, 85, 469-471	1.6	8
4	Magnetic field effect on residual impurity concentrations for LEC GaAs crystal growth. *Journal of Crystal Growth*, **1987**, 84, 247-252	1.6	23
3	Stoichiometry of undoped LEC GaAs. *Journal of Crystal Growth*, **1986**, 79, 463-468	1.6	25
2	Charge-Density-Wave-Like Transition in V3Te4. *Physica Status Solidi (B): Basic Research*, **1983**, 118, K99-K102	1.3	11
1	Transmission Electron Microscopy Study of Single Shockley Stacking Faults in 4H-SiC Expanded from Basal Plane Dislocation Segments Accompanied by Threading Edge Dislocations on both Ends. *Materials Science Forum*,1062, 258-262	0.4	0